L Number	Hits	Search Text	DB	Time stamp
-	1788	micron.as. and circuitry and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 12:04
-	56	(micron.as. and circuitry and capacitor) and crystalline and amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 12:03
-	169	micron.as. and capacitor and crystalline and amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 12:04
-	113	(micron.as. and capacitor and crystalline and amorphous) not ((micron.as. and circuitry and capacitor) and crystalline and amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 12:11
-	285	dielectric with amorphous and dielectric with crystalline and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 12:13
-	2	jp-01315124-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 13:47
-	0	stack adj capacitor with parallel adj plate adj capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 13:48
-	0	stacked adj capacitor with parallel adj plate adj capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 13:50
-	509	(257/303).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 13:51
-	136	((257/303).CCLS.) and parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 13:51
-	90	((257/303).CCLS.) and parallel with (plate electrode capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 13:53
-	1565	stacked with capacitor and parallel with (plate electrode capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 13:54
-	326	stacked with capacitor and parallel adj (plate electrode capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 13:55

–	131	stacked adj capacitor and parallel adj (plate electrode capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 14:00
–	0	stacked adj capacitor with planar adj capacitro	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 14:00
–	82	stacked adj capacitor with planar adj capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 14:10
–	9648	@py>=1999<=2001 and micron.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 14:24
–	1874	(@py>=1999<=2001 and micron.as.) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 14:13
–	288	((@py>=1999<=2001 and micron.as.) and capacitor) and high with dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 14:13
–	7117	@py>=1998<=2000 and micron.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 14:25
–	168	(@py>=1998<=2000 and micron.as.) and capacitor and dielectric with high	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 14:26
–	33	"5972791" "5856704" "5760474"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 19:33
–	61	"5150276"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/01 20:07
–	130	(reduce decrease) with (resistivity resistance) with (source drain) with polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 08:44
–	130	(reduce decrease) with (resistivity resistance) with (source drain) with polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 10:00
–	2	5561307.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 10:00
–	2	5561307.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:28

–	3	"5561307" and matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:28
–	15	"5561307" and array	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:30
–	3459	DRAM with circuit with array	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:31
–	261	DRAM with circuit with matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:31
–	148	DRAM with circuit with array with matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:36
–	149	DRAM with circuit with array and repeat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:38
–	23	DRAM with circuit with array and repeat with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:43
–	11	DRAM with circuit and repeat with cell with unit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:48
–	549	DRAM with circuit with plurality with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:48
–	302	DRAM with circuit with array with plurality with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:51
–	87	(DRAM with circuit with array with plurality with cell) and 257/$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:51
–	15	DRAM with circuit with array with plurality with cell with (conventionally generally typically usually commonly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 12:00
–	23	DRAM with circuit with plurality with cell with (conventionally generally typically usually commonly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:58
–	8	(DRAM with circuit with plurality with cell with (conventionally generally typically usually commonly)) not (DRAM with circuit with array with plurality with cell with (conventionally generally typically usually commonly))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 11:58

–	45	DRAM with array with plurality with cell with (conventionally generally typically usually commonly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 13:29
–	29	(DRAM with array with plurality with cell with (conventionally generally typically usually commonly)) not (DRAM with circuit with array with plurality with cell with (conventionally generally typically usually commonly)) not (DRAM with circuit with plurality with cell with (conventionally generally typically usually commonly))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 12:02
–	0	DRAM with plurality with cell with (conventionally generally typically usually commonly) same row with parallel same column with parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 13:32
–	0	DRAM same plurality with cell same (conventionally generally typically usually commonly) same row with parallel same column with parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 13:34
–	18	DRAM same (conventionally generally typically usually commonly) same row with parallel same column with parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 13:53
–	15	DRAM with (conventional$2 generally typically usually commonly) same row with parallel same column with parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 14:55
–	150	silicon adj dioxide adj amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 14:56
–	33	(silicon adj dioxide adj amorphous) and 257/$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 14:57
–	0	"5150276" and trech	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 18:16
–	33	"5150276" and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 18:27
–	15	"5760474" and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 18:28
–	2	20010015453.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 18:28
–	1	20010015453.pn. and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 18:28

–	2	5864496.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 17:48
–	0	"5561307" and perovskite]	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 17:49
–	31	"5561307" and perovskite	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 17:49